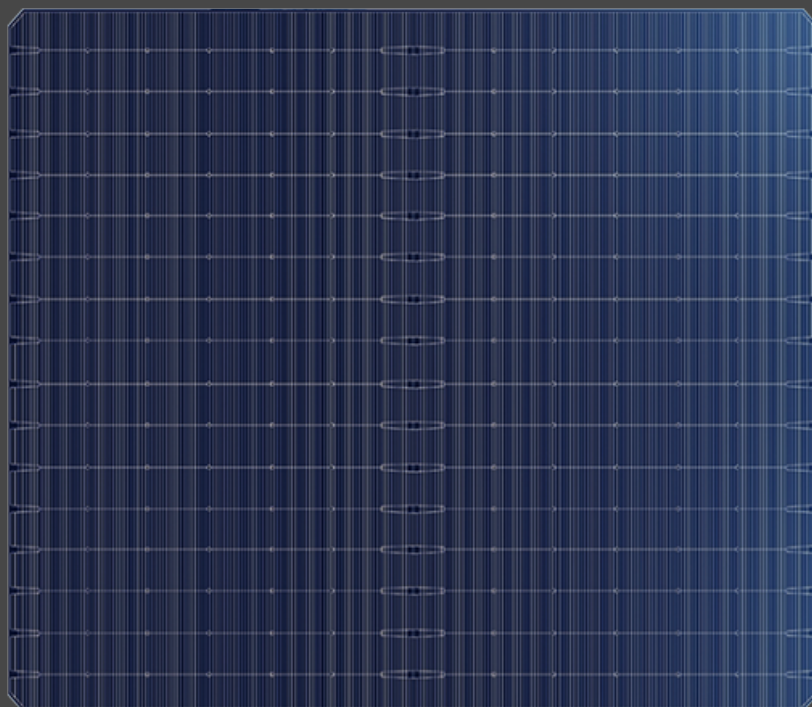




DATASHEET



LX210R-N 16BB



Extremely low light-induced degradation



Strong low-light response



Low temperature poly-Si deposition process



Advanced Laser-enhanced contact optimization



Extremely low light-induced degradation



High module sealed power



Advanced passivation& doping technology



Strong weather resistance



Extremely low light-induced degradation

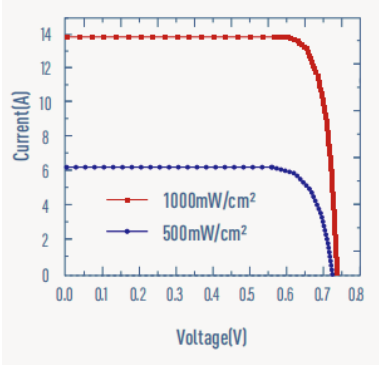
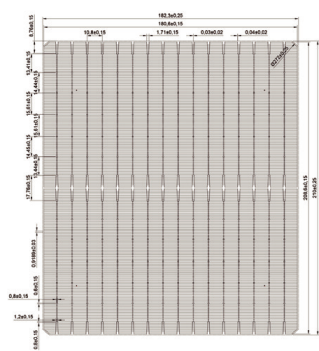
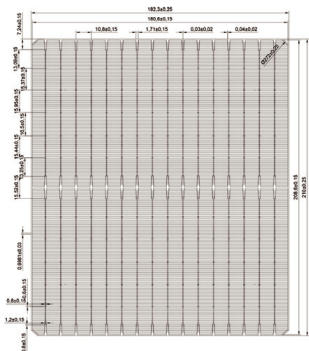
TECHNICAL CHARACTERISTICS

Dimension	210mm*182.3mm±0.5mm Φ272±0.5mm	TkVoltage:-0.26%/K
Thickness	130±13.0μm	TkCurrent:0.046%/K
Front	1.2*0.8/0.8*0.6±0.3 bus bars(silver) black anti-reflecting coating (silicon nitride)	TkPower:-0.30%/K
Back(+)	1.2*0.8/0.8*0.6±0.3 bus bars(silver) black anti-reflecting coating (silicon nitride)	Rsh≥50Ω,Irev2≤0.5A

LIGHT INTENSITY AND RELIABILITY

Intensity(W/m²)	Voc	Isc
1000	1.000	1.000
900	0.996	0.903
800	0.991	0.803
600	0.988	0.602
400	0.962	0.403

The Voc(Isc) tested by 1000W/m2 is the standard, and the Voc(Isc) decreases with the strong decrease in light.



WELDABILITY Minimum peeling intensity ≥0.5N/mm Results may vary depending on the welding ribbon, welding methods and conditions.

ELECTRICAL CHARACTERISTICS

Eff(%)	Pmpp(W)	Vmpp(V)	Ippp(A)	Voc(V)	Isc(A)	FF(%)
26.0	9.93	0.661	15.02	0.739	15.68	85.68
25.9	9.89	0.659	15.01	0.738	15.66	85.57
25.8	9.85	0.658	14.97	0.737	15.65	85.41
25.7	9.81	0.656	14.96	0.735	15.63	85.42
25.6	9.78	0.655	14.92	0.734	15.62	85.26
25.5	9.74	0.654	14.89	0.733	15.61	85.11
25.4	9.70	0.653	14.85	0.732	15.58	85.02
25.3	9.66	0.652	14.82	0.731	15.57	84.90
25.2	9.62	0.650	14.80	0.730	15.56	84.72
25.1	9.58	0.648	14.79	0.729	15.54	84.63
25.0	9.55	0.646	14.78	0.728	15.53	84.43
24.9	9.51	0.643	14.79	0.727	15.51	84.32
24.8	9.47	0.641	14.77	0.725	15.49	84.32
24.7	9.43	0.639	14.76	0.724	15.48	84.15
24.6	9.39	0.638	14.72	0.722	15.47	84.10
24.5	9.36	0.637	14.69	0.721	15.46	83.93